

RQJ0304DQDQS

Silicon P Channel MOS FET Power Switching

REJ03G1778-0100 Rev.1.00 Mar 16, 2009

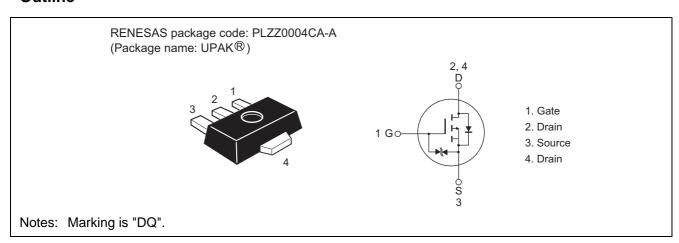
Features

• Low gate drive

 V_{DSS} : -30 V and 2.5 V gate drive

- Low drive current
- High speed switching
- Small traditional Power package (UPAK)

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

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Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	-30	V
Gate to source voltage	V _{GSS}	+8 / -12	V
Drain current	I _D	-2.6	А
Drain peak current	I _{D(pulse)} Note1	-10	А
Body - drain diode reverse drain current	I _{DR}	2.6	А
Channel dissipation	Pch Note2	1.5	W
Thermal resistance	Rth(ch-a) Note2	83	°C /W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \mu s$, Duty cycle $\le 1\%$

2. When using the glass epoxy board (FR-4 $40\times40\times1$ mm)

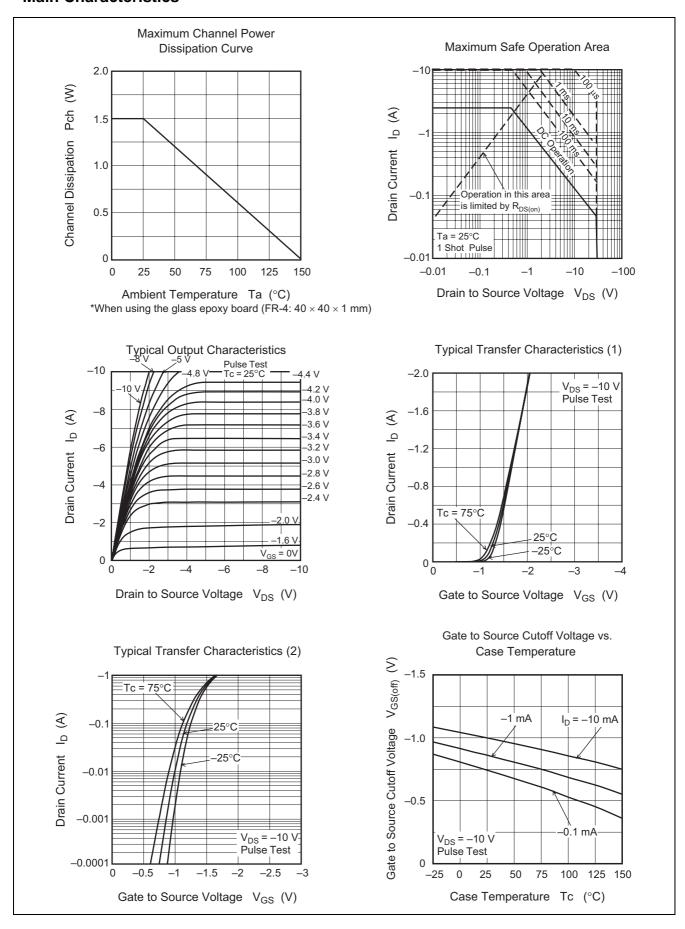
Electrical Characteristics

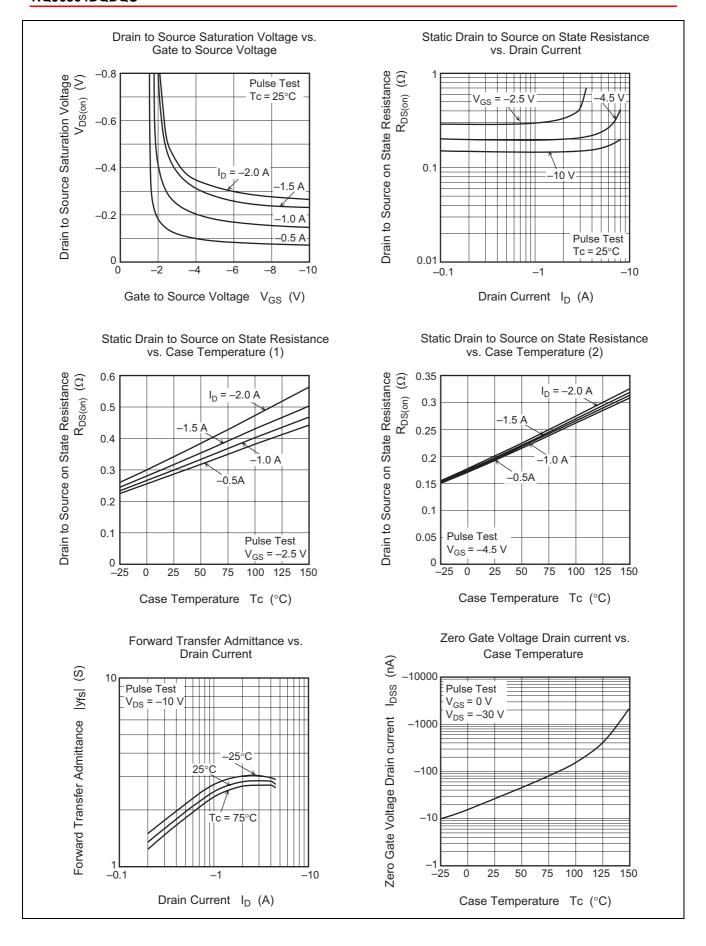
 $(Ta = 25^{\circ}C)$

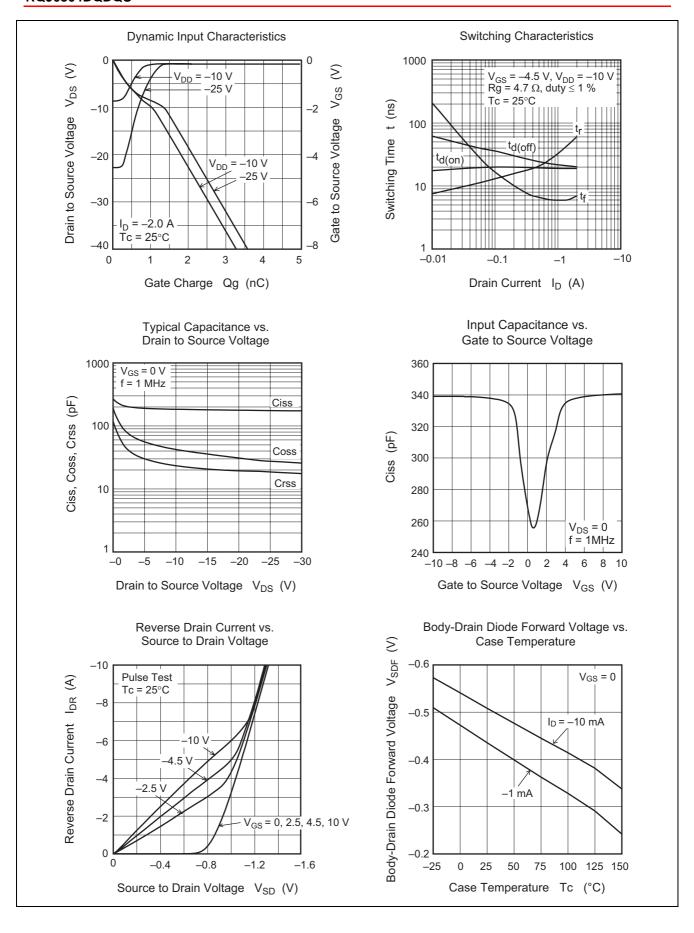
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-30	_	_	V	$I_D = -10 \text{ mA}, V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	+8	_	_	V	$I_G = +100 \mu\text{A}, V_{DS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	-12	_	_	V	$I_G = -100 \mu\text{A}, V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	+10	μΑ	$V_{GS} = +6 \text{ V}, V_{DS} = 0$
Gate to source leak current	I _{GSS}	_	_	-10	μΑ	$V_{GS} = -10 \text{ V}, V_{DS} = 0$
Drain to source leak current	I _{DSS}	_	_	-1	μΑ	$V_{DS} = -30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	-0.4	_	-1.4	V	$V_{DS} = -10 \text{ V}, I_{D} = -1 \text{ mA}$
Drain to source on state resistance	R _{DS(on)}	_	195	245	mΩ	$I_D = -1.3 \text{ A}, V_{GS} = -4.5 \text{ V}^{\text{Note3}}$
Drain to source on state resistance	R _{DS(on)}	_	300	420	mΩ	$I_D = -1.3 \text{ A}, V_{GS} = -2.5 \text{ V}^{\text{Note3}}$
Forward transfer admittance	y _{fs}	1.8	2.5	_	S	$I_D = -1.3 \text{ A}, V_{DS} = -10 \text{ V}^{\text{Note3}}$
Input capacitance	Ciss	_	185	_	pF	$V_{DS} = -10 \text{ V}, V_{GS} = 0,$
Output capacitance	Coss	_	45	_	pF	f = 1 MHz
Reverse transfer capacitance	Crss	_	25	_	pF	
Turn - on delay time	t _{d(on)}	_	18	_	ns	$I_D = -1.0 \text{ A}$
Rise time	t _r	_	33	_	ns	$V_{GS} = -4.5 \text{ V}$
Turn - off delay time	t _{d(off)}	_	22	_	ns	$R_L = 10 \Omega$
Fall time	t _f	_	5	_	ns	$R_g = 4.7 \Omega$
Total gate charge	Qg	_	1.9	_	nC	V _{DD} = -10 V
Gate to Source charge	Qgs	_	0.4	_	nC	$V_{GS} = -4.5 \text{ V}$
Gate to drain charge	Qgd	_	0.7	_	nC	$I_D = -2.0 \text{ A}$
Body - drain diode forward voltage	V_{DF}	_	-0.9	-1.3	V	$I_F = -2.6 \text{ A}, V_{GS} = 0^{\text{Note3}}$

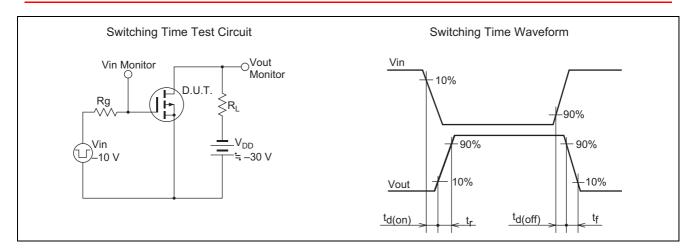
Notes: 3. Pulse test

Main Characteristics

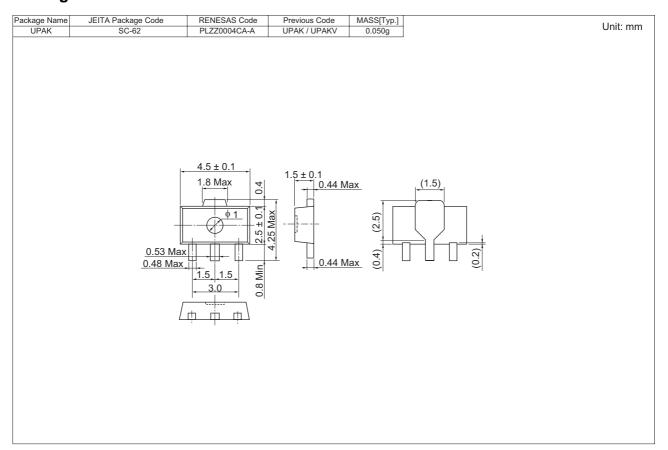








Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RQJ0304DQDQSTL-E	1000 pcs.	φ178 mm reel, 12 mm Emboss taping

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